

Amendments to the Claims:

This listing of claims will replace all prior versions and listings of claims in the application.

Listing of Claims:

1-8. (Cancelled)

9. (Currently Amended) A semiconductor device comprising:

a substrate having a ~~region~~regions irradiated with radiating rays,

crystal defects within the ~~region~~regions irradiated,

impurity regions formed in the substrate, and

a metal wiring layer located over the entire substrate except at [[an]]

~~opening~~openings above the ~~region~~regions irradiated, wherein radiating rays passing to the ~~region~~regions irradiated through the ~~opening~~openings generate the crystal defects under the ~~opening~~openings and so that a smaller amount of radiating rays are irradiated ~~to~~the ~~regions~~elsewhere in said substrate as compared with said ~~region~~regions under the ~~opening~~openings, the metal wiring layer being connected to each of the impurity regions, the metal wiring layer being made of a light metal.

10. (Currently Amended) The semiconductor device in accordance with Claim 9, wherein the metal wiring layer is formed in a thickness so the smaller amount of radiating rays are irradiated ~~to~~the ~~regions~~elsewhere in said substrate except the ~~region~~regions under the ~~opening~~openings.

11. (Currently Amended) The semiconductor device in accordance with Claim 10, wherein an insulating layer is formed above the ~~region~~regions irradiated, the ~~opening~~openings being on the insulating layer.

12. (Previously Presented) The semiconductor device in accordance with Claim 11, wherein the metal wiring layer covers a part of the insulating layer.

13. (Currently Amended) The semiconductor device in accordance with Claim 12, wherein the semiconductor device is an insulated gate bipolar transistor, wherein one of the impurity

~~regionregions~~ is a source region, and wherein one of the regionregions irradiated is a positive-negative junction where a parasitic diode is generated.

14. (Currently Amended) The semiconductor device in accordance with Claim 12, wherein the semiconductor device is a metal oxide semiconductor field effect transistor, wherein one of the impurity regionregions is a source region, and wherein one of the regionregions irradiated is a positive-negative junction region where a parasitic diode is generated.